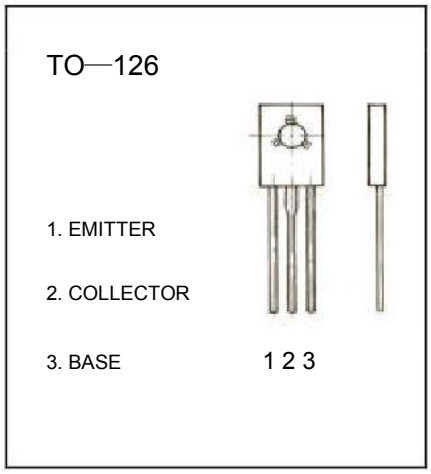
TO-126 Plastic-Encapsulate Transistors

MJE350 TRANSISTOR（ PNP ）



FEATURES

Power dissipation

P_{CM}: 20 W（Tamb=25℃）

Collector current

I_{CM}: -0.5 A

Collector-base voltage

$V_{(BR)CBO}$: -400 V

Operating and storage junction temperature range

T_J，T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS（Tamb=25℃ unless otherwise specified）

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C= 100μA, I_E=0	-400			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C= 1 mA, I_B=0	-300			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E= 100μA, I_C=0	-6			V
Collector cut-off current	I_{CBO}	V_{CB}= 200 V, I_E=0			-500	μA
Collector cut-off current	I_{CEO}	V_{CE}= 200V, I_B=0			-500	μA
Emitter cut-off current	I_{EBO}	V_{EB}= 4 V, I_C=0			-500	μA
DC current gain	H_{FE}	V_{CE}= 10 V, I_C= 10mA	60		300	
Collector-emitter saturation voltage	V_{CE}(sat)	I_C=20mA,I_B= 2 mA			-0.5	V
Base-emitter saturation voltage	V_{BE}(sat)	I_C=20mA, I_B= 2mA			-1	V

Rank						
Range	8-15	15-20	20-25	25-30	30-35	35-40